

IN THE CLAIMS

This is a complete and current listing of the claims, marked with status identifiers in parentheses. The following listing of claims will replace all prior versions and listings of claims in the application.

What is claimed is:

1. (Previously Presented) A semiconductor polishing composition comprising:

fumed silica as abrasive grains,

the semiconductor polishing composition being obtained by preparing a mixture of an acidic aqueous solution and fumed silica having a bulk density of 50 g/L or more and less than 100 g/L, and an alkali aqueous solution so that pH of the mixture is in a range of 1 to 3 and pH of the alkali aqueous solution is in a range of 12 to 14, and adding the mixture to the alkali aqueous solution continuously or intermittently.

2. (Original) The semiconductor polishing composition of claim 1, wherein a content of the fumed silica is in a range of 10% by weight to 30% by weight based on a total amount of the composition.

3. (Cancelled)

4. (Cancelled)

5. (Cancelled)

6. (Currently Amended) The semiconductor polishing composition of claim 1—~~or~~—2, wherein the alkali aqueous solution contains one or two or more additives selected from a polishing accelerator, an oxidant, an organic acid, a complexing agent, a corrosion inhibitor and a surfactant.

7. (Currently Amended) The semiconductor polishing composition of ~~any one of claims 1 to 3~~, wherein alkali contained in the alkali aqueous solution is one or two or more hydroxides selected from ammonium hydroxide, alkali metal hydroxide, and alkaline earth metal hydroxide.

8. (New) The semiconductor polishing composition of claim 2, wherein the alkali aqueous solution contains one or two or more additives selected from a polishing accelerator, an oxidant, an organic acid, a complexing agent, a corrosion inhibitor and a surfactant.

9. (New) The semiconductor polishing composition of claim 2, wherein alkali contained in the alkali aqueous solution is one or two or more hydroxides selected from

ammonium hydroxide, alkali metal hydroxide, and alkaline earth metal hydroxide.

10. (New) The semiconductor polishing composition of claim 3, wherein alkali contained in the alkali aqueous solution is one or two or more hydroxides selected from ammonium hydroxide, alkali metal hydroxide, and alkaline earth metal hydroxide.

11. (New) The semiconductor polishing composition of claim 8, wherein alkali contained in the alkali aqueous solution is one or two or more hydroxides selected from ammonium hydroxide, alkali metal hydroxide, and alkaline earth metal hydroxide.